Ordering number : ENA0399

SANYO Semiconductors
DATA SHEET

CPH3246 — NPN Epitaxial Planar Silicon Transistor
High-Current Switching Applications

Applications

- DC / DC converters, relay drivers, lamp drivers, motor drivers, inverters.

Features

- Adoption of FBET, MBIT processes.
- Large current capacitance.
- Low collector-to-emitter saturation voltage.
- High-speed switching.
- Ultrasmall package permitting applied sets to be small and slim (mounting height: 0.9mm).
- High allowable power dissipation.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		100	V
Collector-to-Emitter Voltage	V_{CES}		100	V
Collector-to-Emitter Voltage	V_{CEO}		60	V
Emitter-to-Base Voltage	V_{EBO}		6.5	V
Collector Current	I_C		3	A
Collector Current (Pulse)	I_{CP}		5	A
Base Current	I_B		600	mA
Collector Dissipation	P_C	Mounted on a ceramic board (600mm²×0.8mm)	0.9	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	V_{CB}=50V, I_E=0A			1	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=4V, I_C=0A			1	μA
DC Current Gain	h_{FE}	V_{CE}=2V, I_C=100mA	300		600	
Gain-Bandwidth Product	f_T	V_{CE}=10V, I_C=500mA		390		MHz
Output Capacitance	Cob	V_{CB}=10V, f=1MHz		15		pF

Marking : DR

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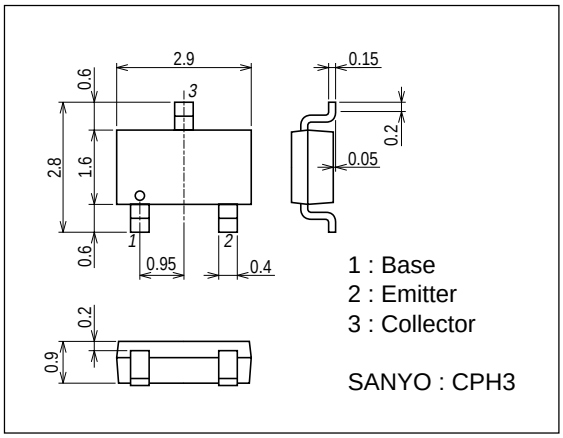
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector-to-Emitter Saturation Voltage	$V_{CE}(sat)1$	I_C=1A, I_B=50mA		80	120	mV
	$V_{CE}(sat)2$	I_C=1A, I_B=100mA		70	110	mV
Base-to-Emitter Saturation Voltage	$V_{BE}(sat)$	I_C=1A, I_B=100mA		0.85	1.2	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=10μA, I_E=0A	100			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CES}$	I_C=100μA, R_{BE}=0Ω	100			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=1mA, R_{BE}=∞	60			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=10μA, I_C=0A	6.5			V
Turn-ON Time	t_{on}	See specified Test Circuit.		35		ns
Storage Time	t_{stg}	See specified Test Circuit.		680		ns
Fall Time	t_f	See specified Test Circuit.		24		ns

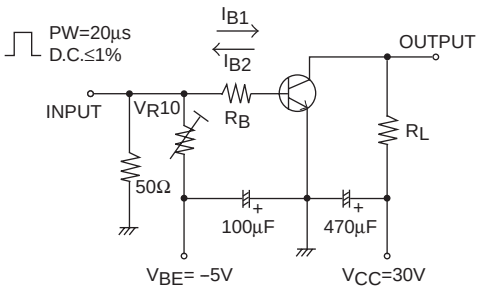
Package Dimensions

unit : mm

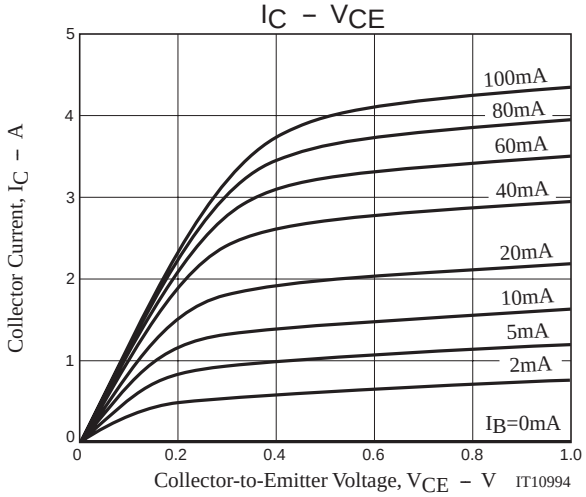
7015A-003

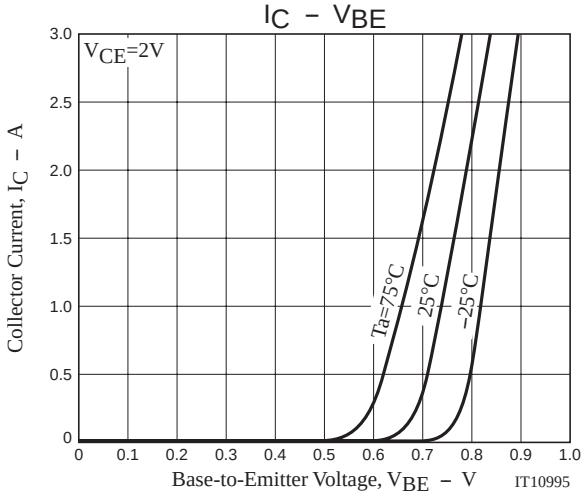


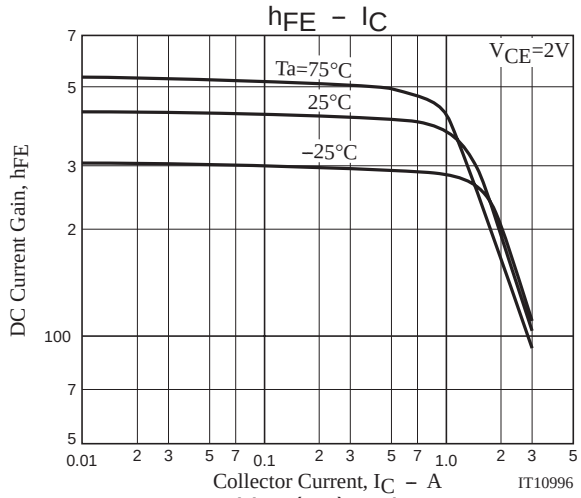
Switching Time Test Circuit

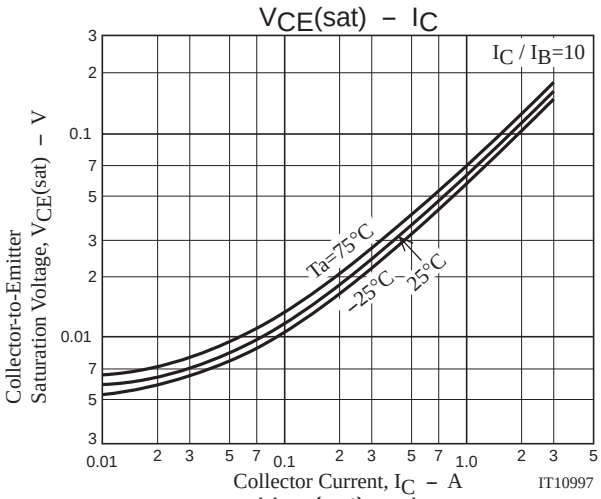


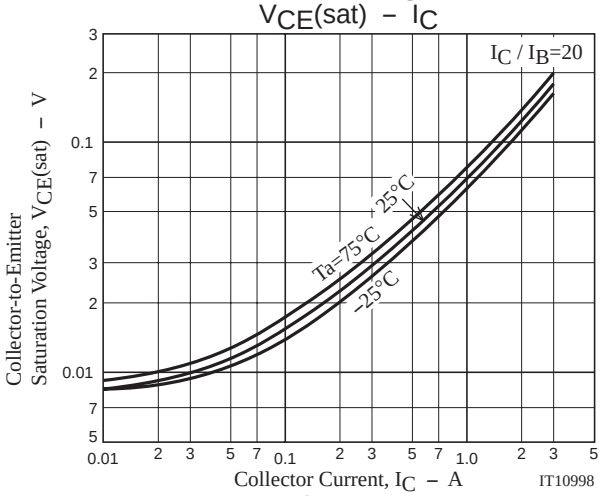
$10I_{B1}$= −$10I_{B2}$=I_C=0.5A

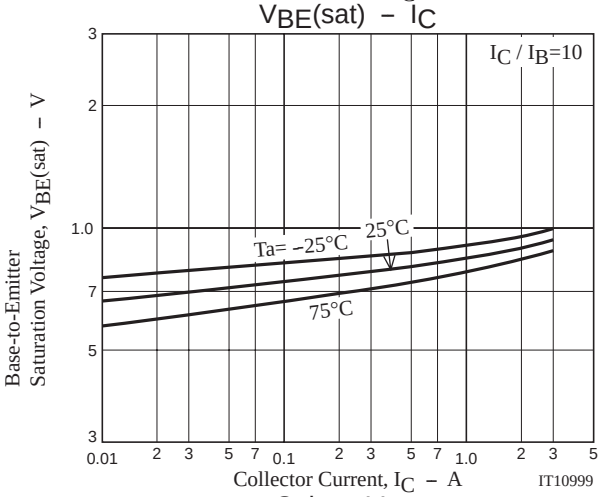


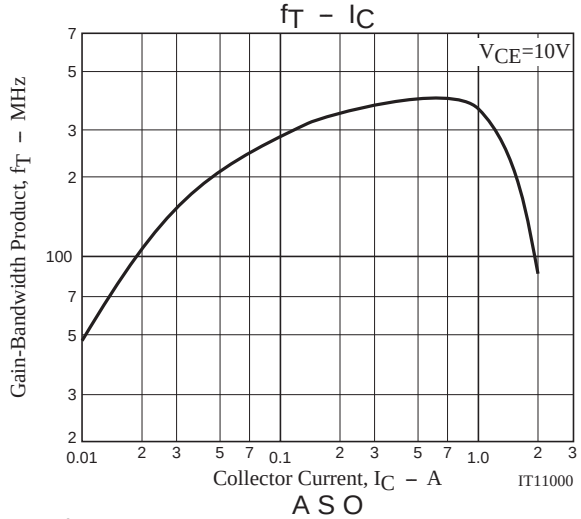


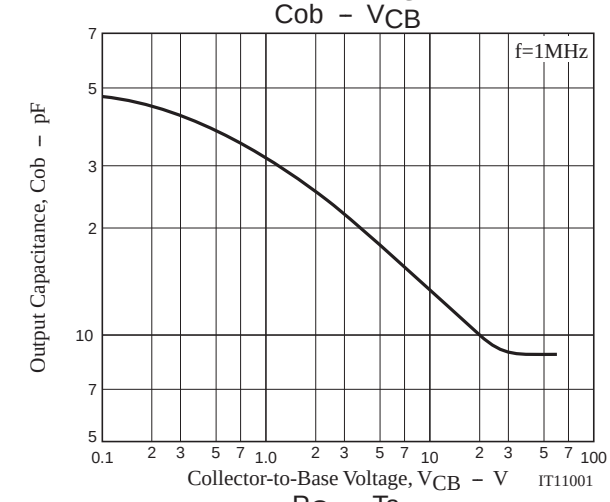

hFE – IC
VCE=2V
Ta=75°C
25°C
–25°C
DC Current Gain, hFE
Collector Current, IC – A
IT10996

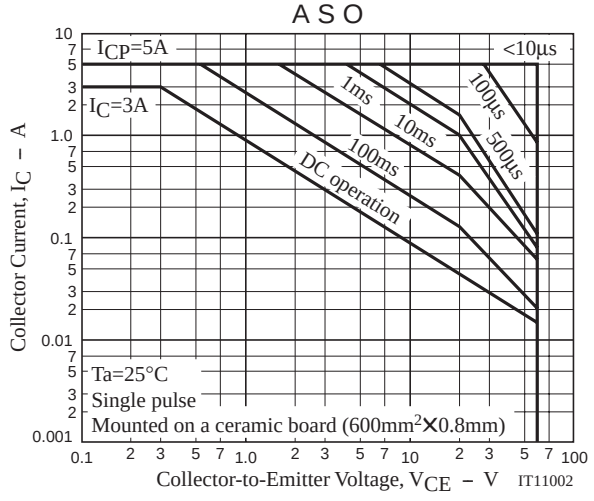

VCE(sat) – IC
IC / IB=10
Ta=75°C
25°C
–25°C
Collector-to-Emitter Saturation Voltage, VCE(sat) – V
Collector Current, IC – A
IT10997

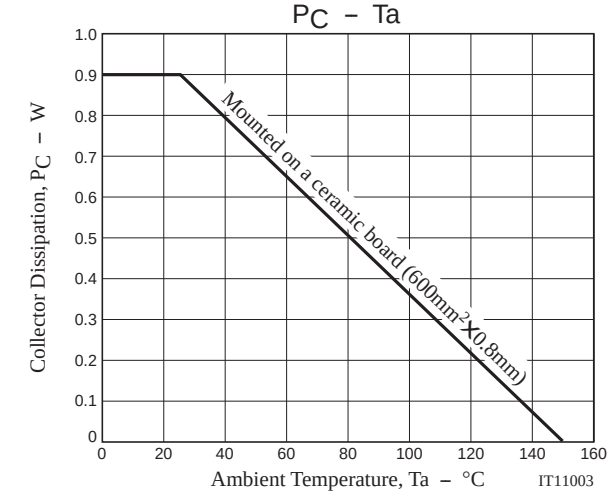

VCE(sat) – IC
IC / IB=20
Ta=75°C
25°C
–25°C
Collector-to-Emitter Saturation Voltage, VCE(sat) – V
Collector Current, IC – A
IT10998


VBE(sat) – IC
IC / IB=10
Ta= –25°C
25°C
75°C
Base-to-Emitter Saturation Voltage, VBE(sat) – V
Collector Current, IC – A
IT10999


fT – IC
VCE=10V
Gain-Bandwidth Product, fT – MHz
Collector Current, IC – A
IT11000


Cob – VCB
f=1MHz
Output Capacitance, Cob – pF
Collector-to-Base Voltage, VCB – V
IT11001


A S O
ICP=5A
IC=3A
<10µs
100µs
1ms
10ms
500µs
100ms
DC operation
Ta=25°C
Single pulse
Mounted on a ceramic board (600mm²×0.8mm)
Collector Current, IC – A
Collector-to-Emitter Voltage, VCE – V
IT11002


PC – Ta
Mounted on a ceramic board (600mm²×0.8mm)
Collector Dissipation, PC – W
Ambient Temperature, Ta – °C
IT11003